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Power Matters[™]

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Overview Diagrams

Collector to Emitter Saturation Voltage

Sumbol Min T

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			100.00	V
Collector Current (dc)	I _C			5.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			80.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.00	V
Power Discipation Total	D_			30.00	\//

V_{CE(sat)}

0.50

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ NPN Transistor

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